

Sensitivity of Al-Doped Zinc-Oxide Extended Gate Field Effect Transistors to Low-Dose X ray Radiation

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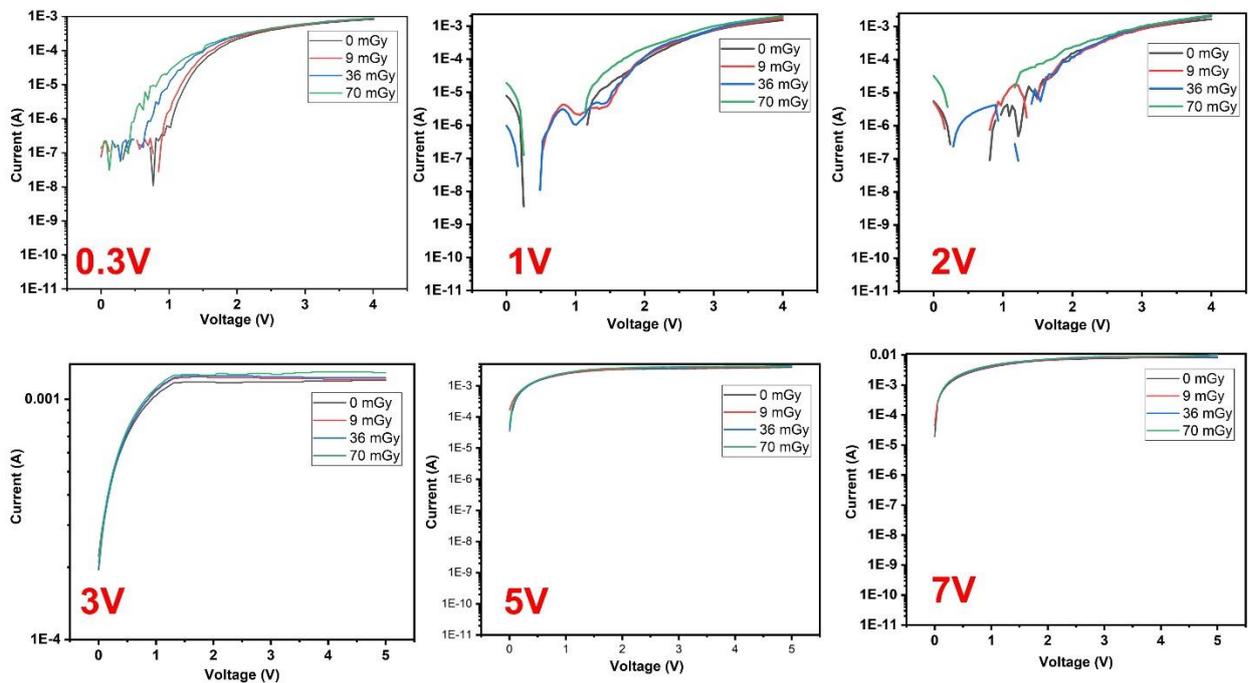


Figure S1. Transfer characteristics in the y-log scale for the used biased voltages, the graphs give more data concerning off-current, subthreshold swing, and threshold voltage).